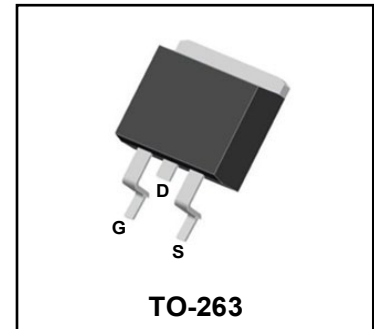


65V N-Channel Enhancement Mode Power MOSFET

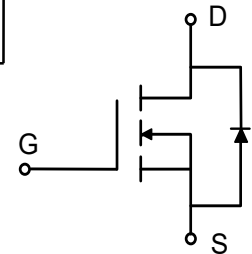
Description

WMM048NV6HG4 uses Wayon's 4th generation power trench MOSFET technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance. This device is well suited for high efficiency fast switching applications.



Features

- $V_{DS} = 65V$, $I_D = 110A$
 $R_{DS(on)} < 5.2m\Omega @ V_{GS} = 10V$
- Green Device Available
- 100% EAS Guaranteed
- Low $R_{ds(on)}$



Applications

- Synchronous Rectification
- DC/DC Converter

Absolute Maximum Ratings ($T_A = 25^\circ C$, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	65	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C = 25^\circ C$	110
		$T_C = 100^\circ C$	70
Pulsed Drain Current ¹	I_{DM}	440	A
Single Pulse Avalanche Energy ²	EAS	80	mJ
Total Power Dissipation	P_D	104.2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	$R_{\theta JA}$	52	$^\circ C/W$
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	1.2	$^\circ C/W$

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	65	-	-	V
Gate-body Leakage Current		I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T _J =25°C	I _{DSS}	V _{DS} = 65V, V _{GS} = 0V	-	-	1	μA
	T _J =100°C			-	-	100	
Gate-Threshold Voltage		V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2	2.9	4	V
Drain-Source On-Resistance ⁴		R _{DS(on)}	V _{GS} = 10V, I _D = 20A	-	4	5.2	mΩ
Forward Transconductance ⁴		g _{fs}	V _{DS} = 10V, I _D = 20A	-	89	-	S
Dynamic Characteristics⁵							
Input Capacitance	C _{iss}	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	-	1675	-	pF	
Output Capacitance	C _{oss}		-	772	-		
Reverse Transfer Capacitance	C _{rss}		-	46.5	-		
Gate Resistance	R _g	f = 1MHz	-	1.8	-	Ω	
Switching Characteristics⁵							
Total Gate Charge	Q _g	V _{GS} = 10V, V _{DS} = 30V, I _D = 20A	-	28.5	-	nC	
Gate-Source Charge	Q _{gs}		-	7.8	-		
Gate-Drain Charge	Q _{gd}		-	8.4	-		
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DD} = 30V, R _G = 3Ω, I _D = 20A	-	11.2	-	ns	
Rise Time	t _r		-	8.2	-		
Turn-Off Delay Time	t _{d(off)}		-	19.6	-		
Fall Time	t _f		-	6.2	-		
Body Diode Reverse Recovery Time	t _{rr}	I _F = 20A, dI/dt = 100A/μs	-	50	-	ns	
Body Diode Reverse Recovery Charge	Q _{rr}		-	20	-	nC	
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴		V _{SD}	I _S = 20A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	T _C = 25°C	I _S	-	-	-	110	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)} = 150°C
2. The EAS data shows Max. rating . The test condition is V_{DD} = 25V, V_{GS} = 10V, L = 0.1mH, I_{AS} = 40A.
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

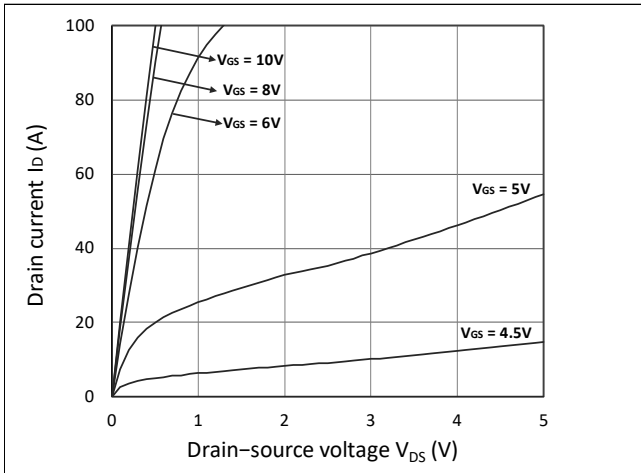


Figure 1. Output Characteristics

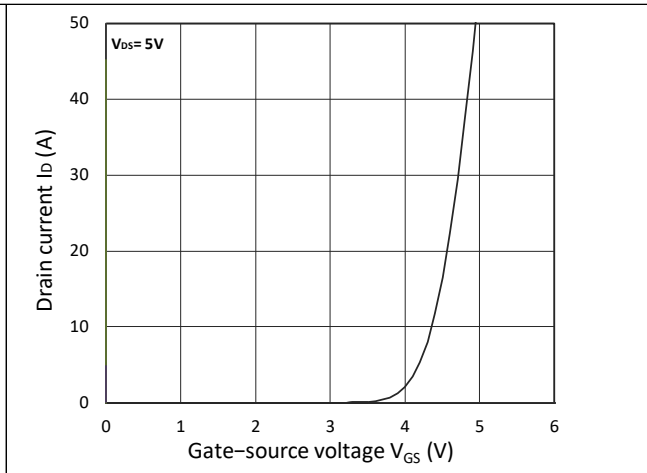


Figure 2. Transfer Characteristics

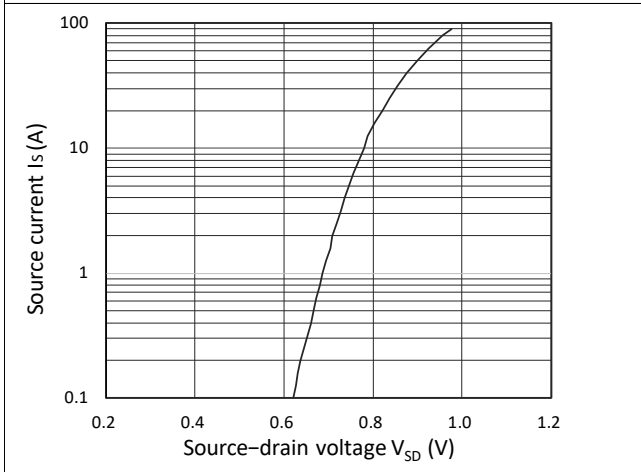


Figure 3. Forward Characteristics of Reverse

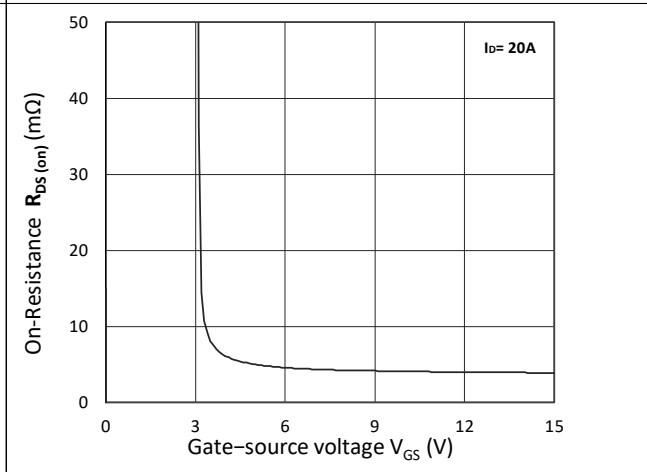


Figure 4. $R_{DS(on)}$ vs. V_{GS}

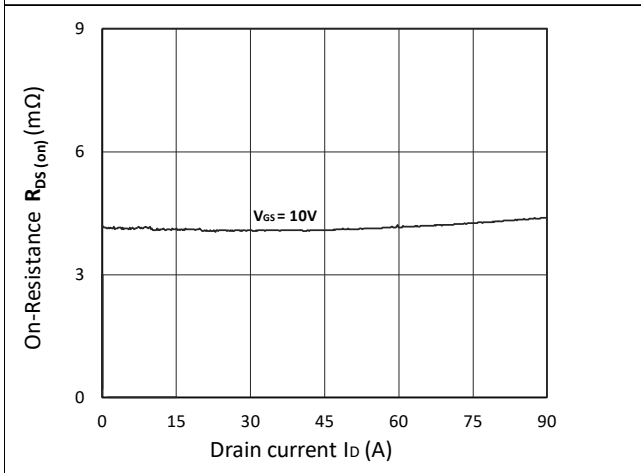


Figure 5. $R_{DS(on)}$ vs. I_D

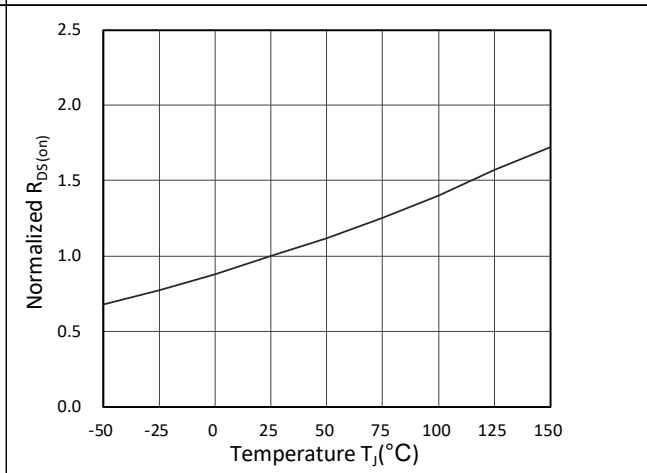


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

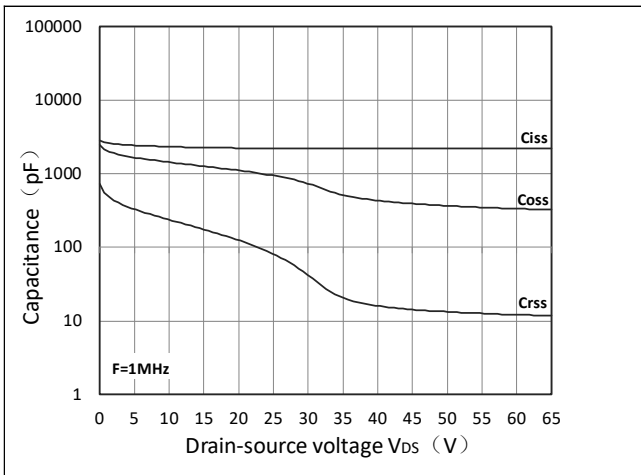


Figure 7. Capacitance Characteristics

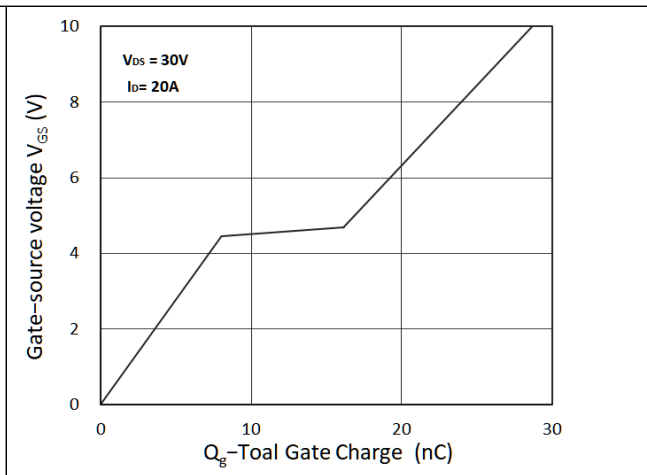


Figure 8. Gate Charge Characteristics

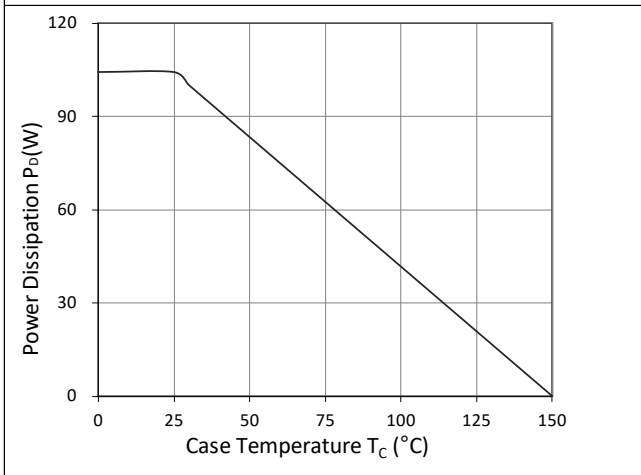


Figure 9. Power Dissipation

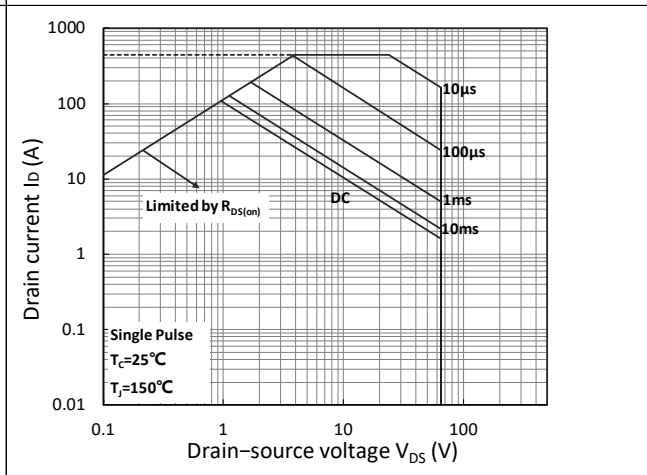


Figure 10. Safe Operating Area

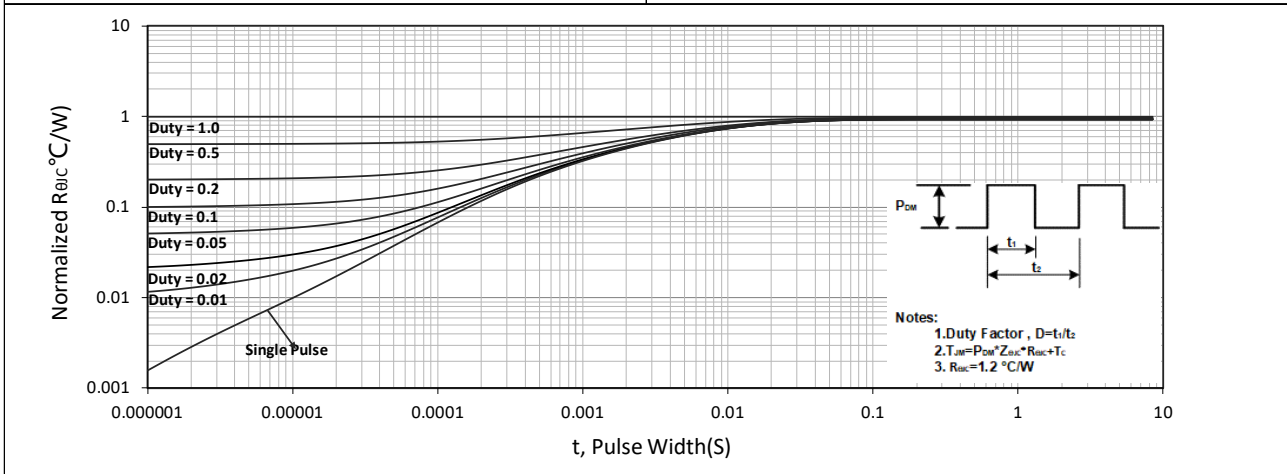


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

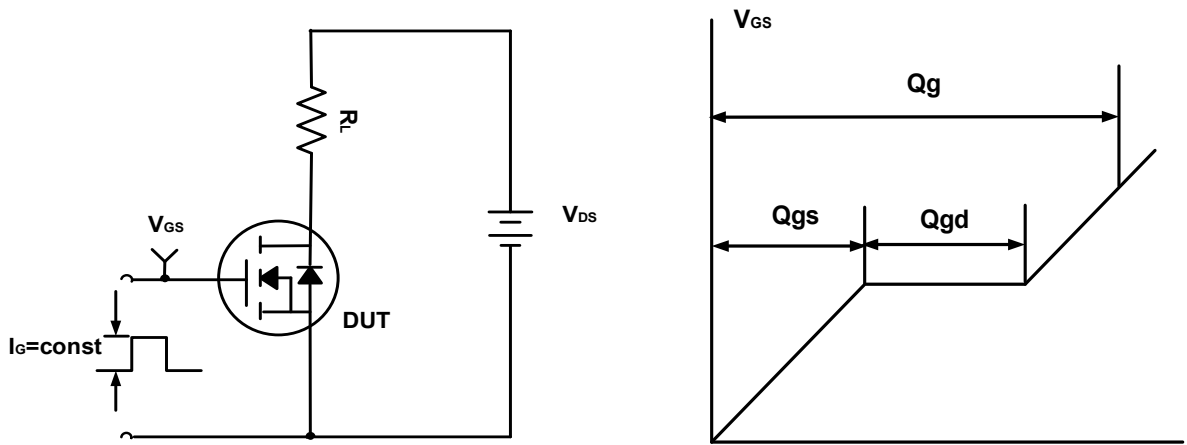


Figure A. Gate Charge Test Circuit & Waveforms

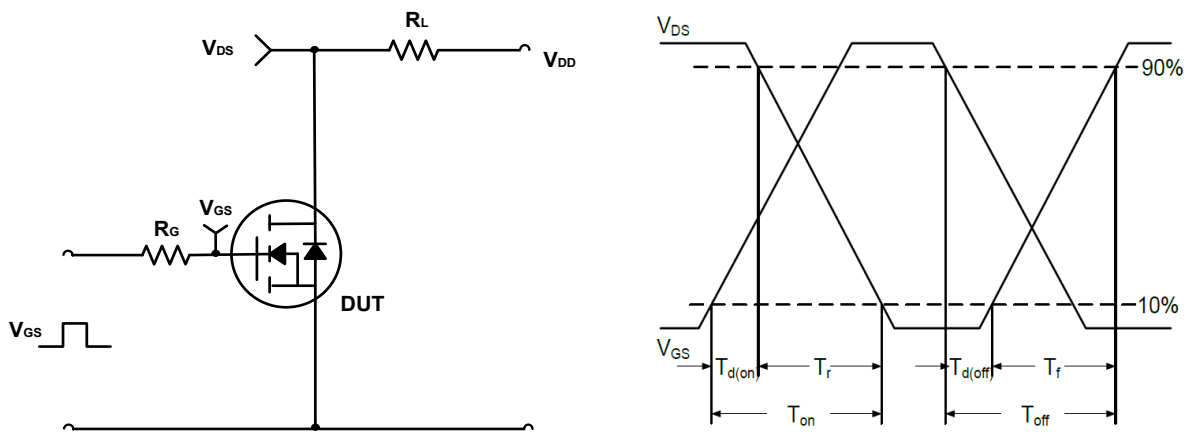


Figure B. Switching Test Circuit & Waveforms

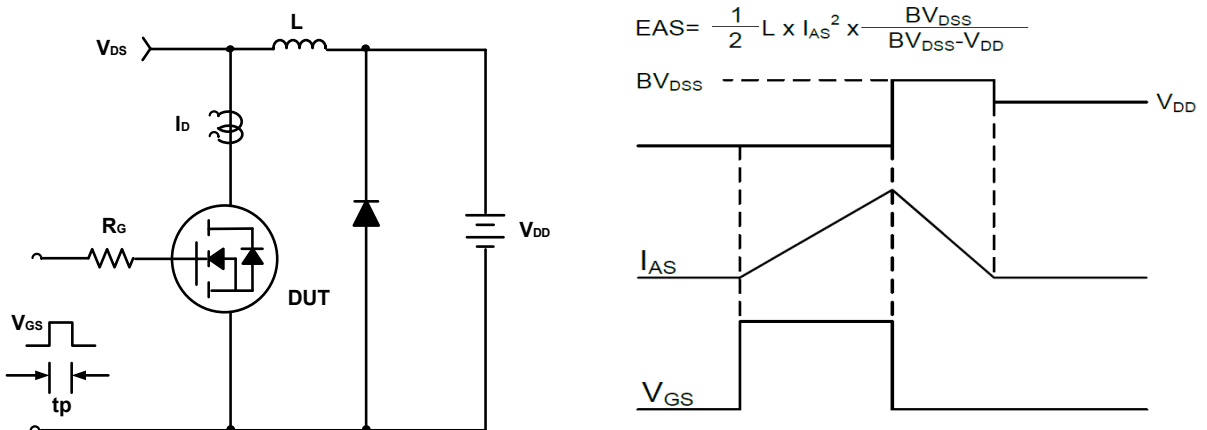
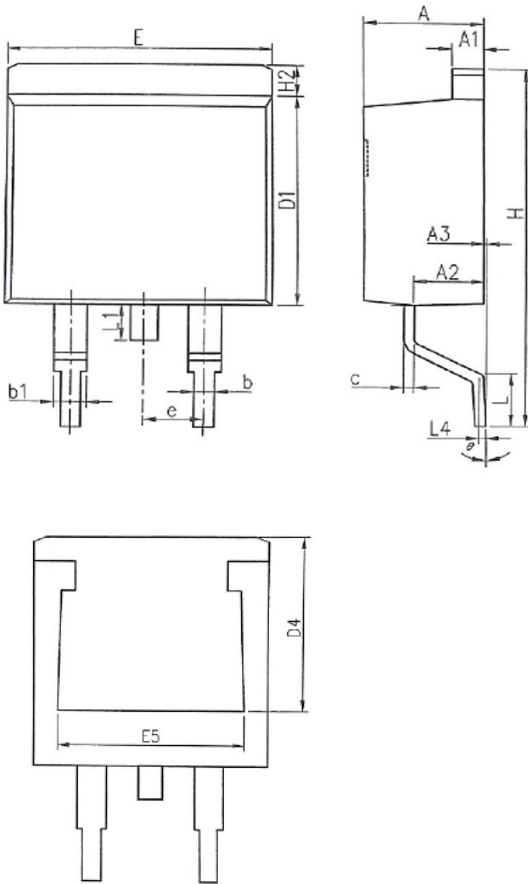


Figure C. Unclamped Inductive Switching Circuit & Waveforms

Mechanical Dimensions for TO-263

COMMON DIMENSIONS

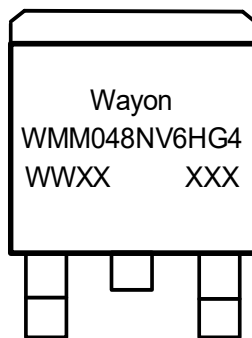


SYMBOL	MM	
	MIN	MAX
A	4.37	4.89
A1	1.17	1.42
A2	2.20	2.90
A3	0.00	0.25
b	0.70	0.96
b1	1.17	1.47
c	0.28	0.60
D1	8.45	9.30
D4	6.60	-
E	9.80	10.40
E5	7.06	-
e	2.54BSC	
H	14.70	15.70
H2	1.07	1.47
L	2.00	2.80
L1	-	1.75
L4	0.254BSC	
θ	0°	9°

Ordering Information

Part	Package	Marking	Packing method
WMM048NV6HG4	TO-263	WMM048NV6HG4	Tape and Reel

Marking Information



WMM048NV6HG4= Device code

WWXX XXX= Date code


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